PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q81061

Hideki HAYASHIDA, et al.

Appln. No.: Not Yet Assigned

Group Art Unit: 1765 (parent)

Continuation of 09/473,708 filed December 29, 1999

Confirmation No.: Not Yet Assigned

Examiner: Robert Kunemund (parent)

Filed: April 12, 2004

For:

AMMONIA FOR USE IN MANUFACTURE OF GAN-TYPE COMPOUND SEMICONDUCTOR AND METHOD FOR MANUFACTURING GAN-TYPE

COMPOUND SEMICONDUCTOR

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR §§ 1.97 and 1.98

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 CFR §1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form which are all the references of record in parent application No. 09/473,708. Applicant is not submitting duplicate copies of these references but requests that they be listed on the face of any patent granted on the above application. 37 CFR §1.98(d)). Copies of any cited copending applications, if not previously submitted, are being submitted herewith.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

Respectfully submitted,

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WASHINGTON OFFICE 23373
CUSTOMER NUMBER

Date: April 12, 2004

					MODIFIED PTO/SB/08 A & B (08-03			
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Substitute for Form 1449 A & B/PTO					Not Yet Assigned (Continuation of U.S. Application No.			
INFOR	RMATION	DISCLOS	SURE	Application Number	09/473,708)			
STATI	EMENT BY	APPLIC	CANT	Confirmation Number	Not Yet Assigned			
				Filing Date	April 12, 2004			
(use	as many sheet	s as necessa	ry)	First Named Inventor	Hideki HAYASHIDA, et al.			
				Art Unit	1786 (parent)			
				Examiner Name	Robert Kunemund (parent)			
Sheet	1	of	1	Attorney Docket Numb	per Q81061			

U.S. PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Document Number		Publication Date			
		Number	Kind Code ² (if known)	MM-DD-YYYY	Name of Patentee or Applicant of Cited Document		
		US 3,931,631		1-1976	Groves et al		
		US 4,001,056		1-1977	Groves et al		
		US 5,716,588		2-1998	Vergani et al		
		US 5,831,277		11-1998	Razeghi		
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.1	Foreign Patent Document			Publication Date	Name of Patentee or	
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant of Cited Document	Translation ⁶
		JР	09-251957		09-22-1997		
		EP	0 662 339	A2	01-09-1995		
		JР	08-201370	1	08-09-1996		Abstract
		ЛР	09-142833		06-03-1997		Abstract
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NON PATENT LITERATURE DOCUMENTS					
Examiner Cite Initials* No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.				
-	_	Patent Abstract of Japan, JP 09-251957, dated 9/22/1997			
		Hiebuhr et al, "Electrical and Optical Properties of Oxygen Doped GaN Grown by MOCVD using N2O", Journal of Electronic Materials, vol. 26, no. 10 (10/1997)			

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Examiner Signature		Data Canaidanad		
Digitatui C		Date Considered	1	
			 	

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or follow the hyperlink from the title of the document to the intranet. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.